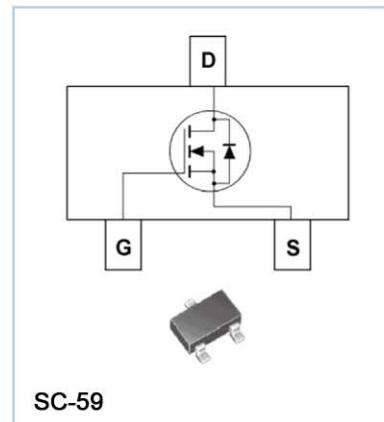


### Feature

- 16V/3.6A, R<sub>DS(ON)</sub> = 80m Ω (MAX) @V<sub>GS</sub> = 4.5V.  
R<sub>DS(ON)</sub> = 90m Ω (MAX) @V<sub>GS</sub> = 2.5V.
- Super High dense cell design for extremely low R<sub>DS(ON)</sub>.
- Reliable and Rugged.
- SC-59 for Surface Mount Package.



### Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

### Absolute Maximum Ratings

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V <sub>DS</sub>	16	V
Gate-Source Voltage	V <sub>GS</sub>	±8	V
Drain Current-Continuous	I <sub>D</sub>	3.6	A

### Electrical Characteristics

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V, ID=250 μA	16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =12V, V <sub>GS</sub> =0V	-	-	1	μA
Gate Body Leakage Current, Forward	IGSSF	V <sub>GS</sub> =8V, V <sub>DS</sub> =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V <sub>GS</sub> =-8V, V <sub>DS</sub> =0V	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , ID=250μA	0.4	-	1.3	V
Static Drain-source	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, ID = 3.6A	-	70	80	m Ω
On-Resistance		V <sub>GS</sub> = 2.5V, ID = 3.1A	-	75	90	m Ω
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, IS=0.94A			1.2	V

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## Typical Characteristics

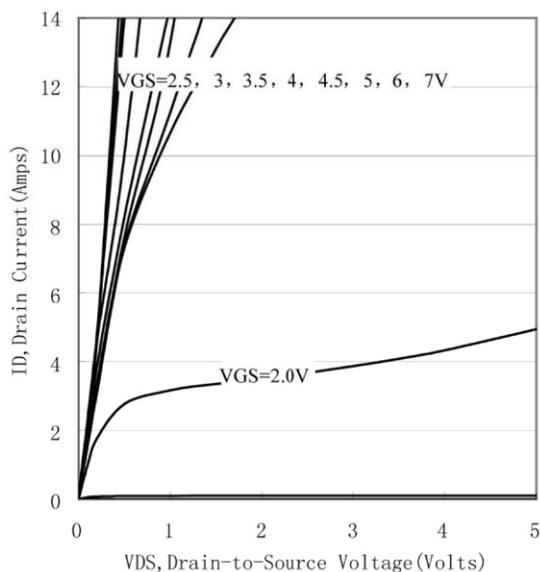


Figure 1. Output Characteristics

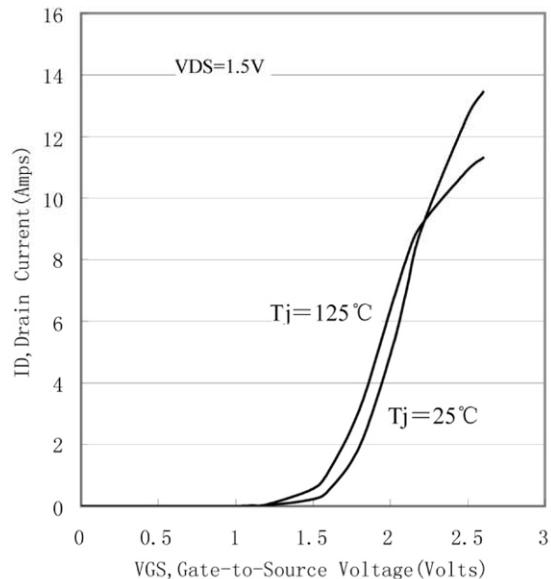


Figure 2. Transfer Characteristics

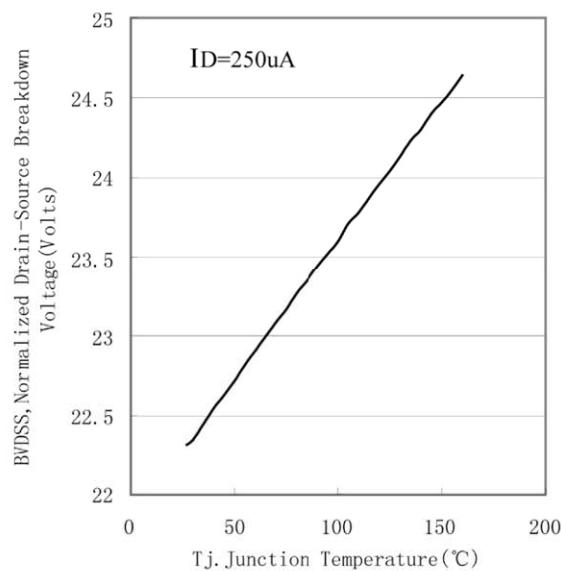


Figure 3. Breakdown Voltage Variation with Temperature

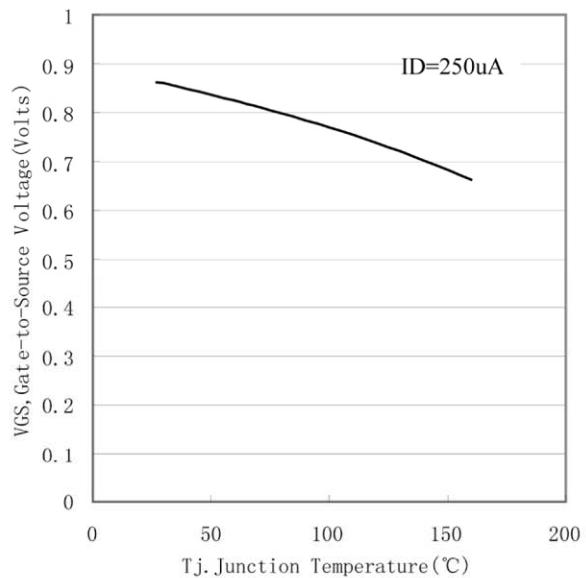
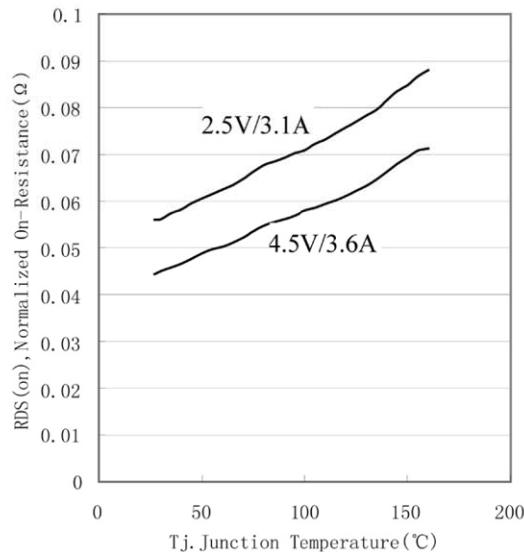
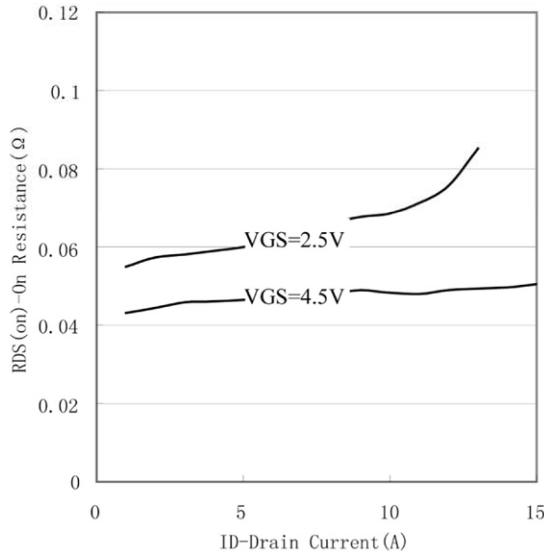


Figure 4. Gate Threshold Variation with Temperature

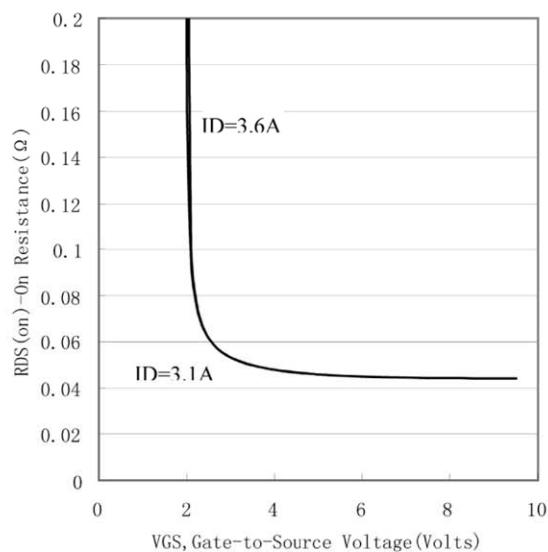
## Typical Characteristics



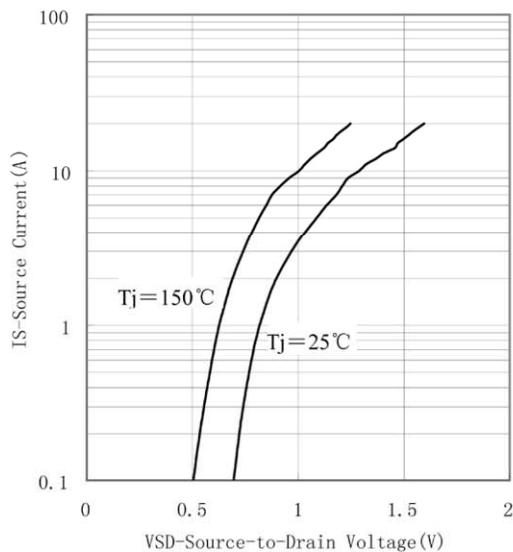
**Figure 5. On-Resistance Variation with Temperature**



**Figure 6. On-Resistance vs. Drain Current**



**Figure 7. On-Resistance vs. Gate-to-Source Voltage**



**Figure 8. Source-Drain Diode Forward Voltage**

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